

# MMBT4403LT1

Preferred Device

## Switching Transistor

### PNP Silicon

#### Features

- Pb-Free Packages are Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–600	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

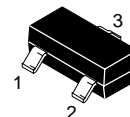
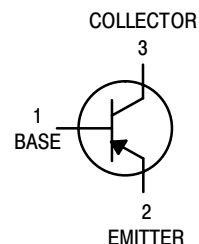
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



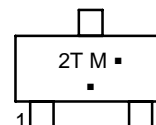
ON Semiconductor®

<http://onsemi.com>



SOT–23 (TO–236)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



2T = Specific Device Code  
M = Date Code\*  
■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT4403LT1	SOT–23	3000 Tape & Reel
MMBT4403LT1G	SOT–23 (Pb–Free)	3000 Tape & Reel
MMBT4403LT3	SOT–23	10,000 Tape & Reel
MMBT4403LT3G	SOT–23 (Pb–Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MMBT4403LT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = –1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	–40	–	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = –0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	–40	–	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –0.1 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	–5.0	–	Vdc
Base Cutoff Current (V <sub>CE</sub> = –35 Vdc, V <sub>EB</sub> = –0.4 Vdc)	I <sub>BEV</sub>	–	–0.1	μAdc
Collector Cutoff Current (V <sub>CE</sub> = –35 Vdc, V <sub>EB</sub> = –0.4 Vdc)	I <sub>CEX</sub>	–	–0.1	μAdc

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = –0.1 mAdc, V <sub>CE</sub> = –1.0 Vdc) (I <sub>C</sub> = –1.0 mAdc, V <sub>CE</sub> = –1.0 Vdc) (I <sub>C</sub> = –10 mAdc, V <sub>CE</sub> = –1.0 Vdc) (Note 3) (I <sub>C</sub> = –150 mAdc, V <sub>CE</sub> = –2.0 Vdc) (Note 3) (I <sub>C</sub> = –500 mAdc, V <sub>CE</sub> = –2.0 Vdc)	h <sub>FE</sub>	30 60 100 100 20	– – – 300 –	–
Collector–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –150 mAdc, I <sub>B</sub> = –15 mAdc) (I <sub>C</sub> = –500 mAdc, I <sub>B</sub> = –50 mAdc)	V <sub>CE(sat)</sub>	– –	–0.4 –0.75	Vdc
Base–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –150 mAdc, I <sub>B</sub> = –15 mAdc) (I <sub>C</sub> = –500 mAdc, I <sub>B</sub> = –50 mAdc)	V <sub>BE(sat)</sub>	–0.75 –	–0.95 –1.3	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = –20 mAdc, V <sub>CE</sub> = –10 Vdc, f = 100 MHz)	f <sub>T</sub>	200	–	MHz
Collector–Base Capacitance (V <sub>CB</sub> = –10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	–	8.5	pF
Emitter–Base Capacitance (V <sub>BE</sub> = –0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>eb</sub>	–	30	pF
Input Impedance (I <sub>C</sub> = –1.0 mAdc, V <sub>CE</sub> = –10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	1.5	15	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = –1.0 mAdc, V <sub>CE</sub> = –10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	8.0	X 10 <sup>–4</sup>
Small–Signal Current Gain (I <sub>C</sub> = –1.0 mAdc, V <sub>CE</sub> = –10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	60	500	–
Output Admittance (I <sub>C</sub> = –1.0 mAdc, V <sub>CE</sub> = –10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	100	μMhos

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = –30 Vdc, V <sub>EB</sub> = –2.0 Vdc, I <sub>C</sub> = –150 mAdc, I <sub>B1</sub> = –15 mAdc)	t <sub>d</sub>	–	15	ns
Rise Time		t <sub>r</sub>	–	20	
Storage Time	(V <sub>CC</sub> = –30 Vdc, I <sub>C</sub> = –150 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = –15 mAdc)	t <sub>s</sub>	–	225	ns
Fall Time		t <sub>f</sub>	–	30	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

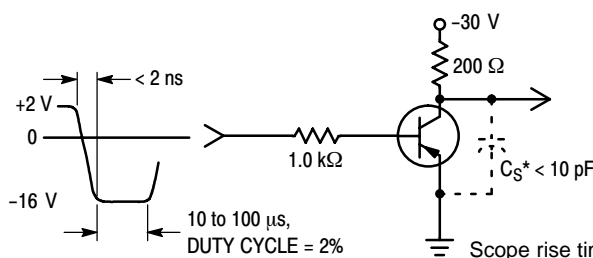


Figure 1. Turn–On Time

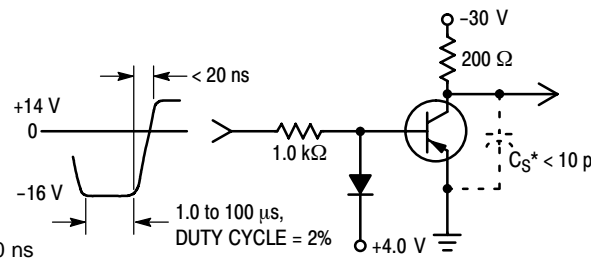


Figure 2. Turn–Off Time

# MMBT4403LT1

## TRANSIENT CHARACTERISTICS

— 25°C    - - - 100°C

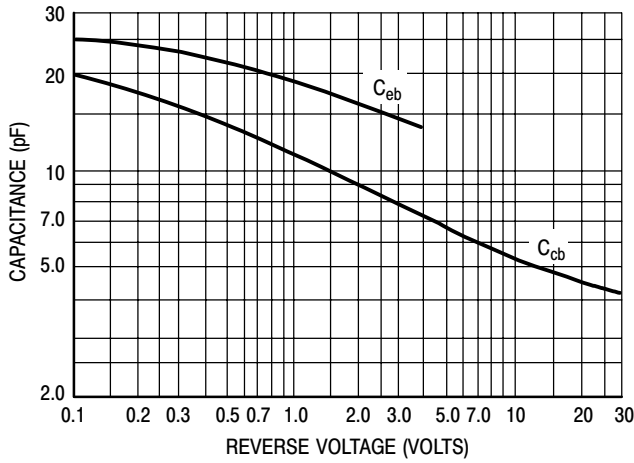


Figure 3. Capacitances

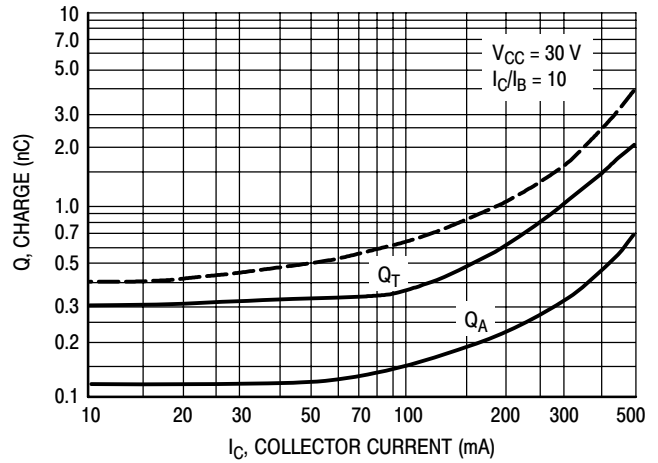


Figure 4. Charge Data

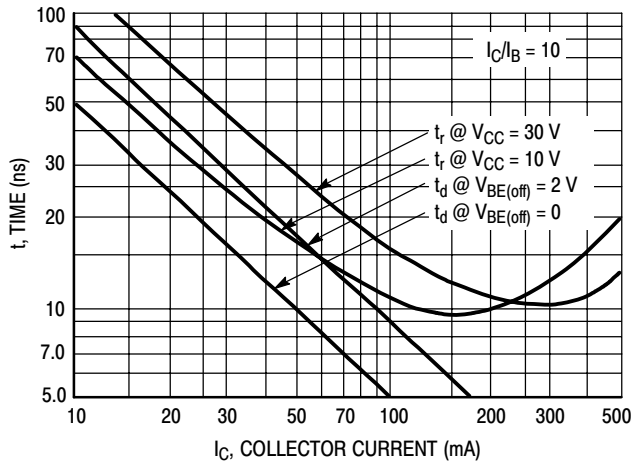


Figure 5. Turn-On Time

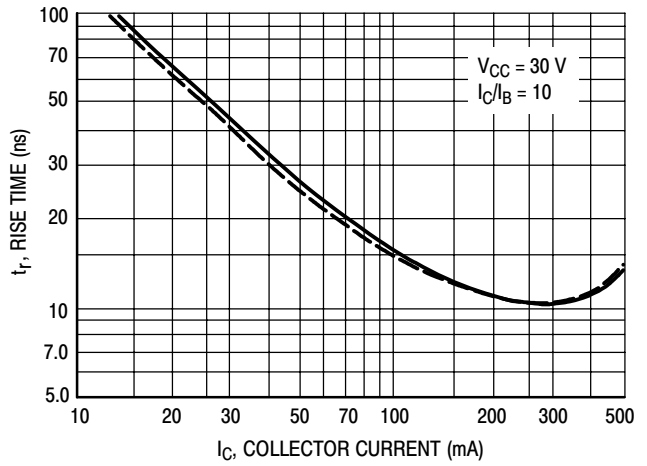


Figure 6. Rise Time

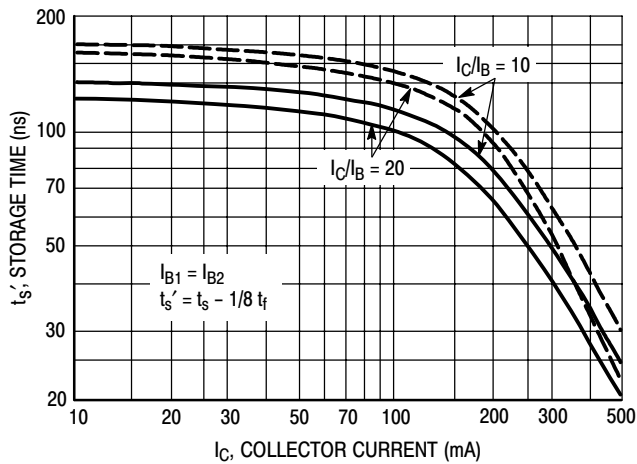


Figure 7. Storage Time

# MMBT4403LT1

## SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ ; Bandwidth = 1.0 Hz

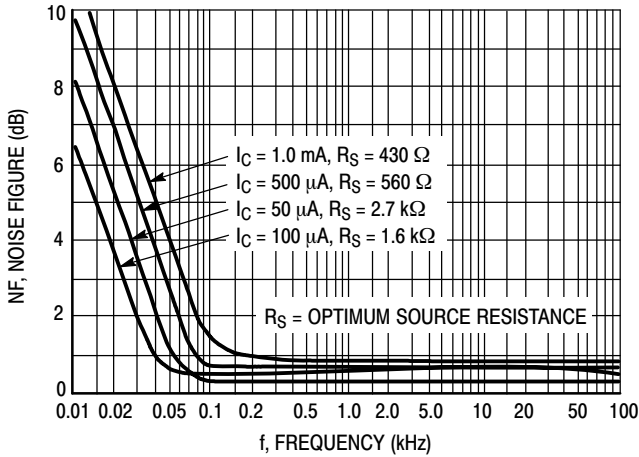


Figure 8. Frequency Effects

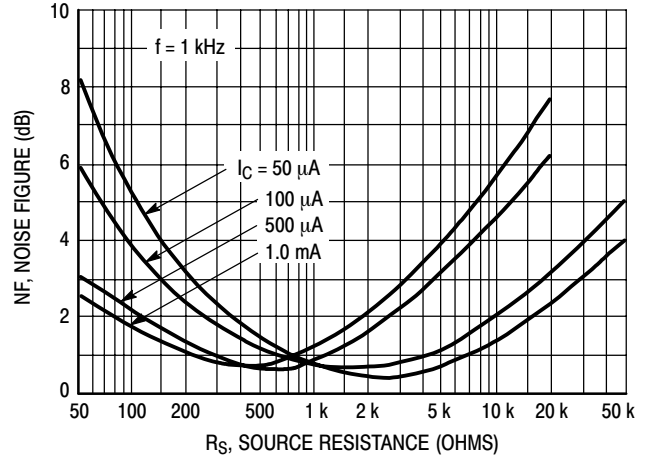


Figure 9. Source Resistance Effects

## h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

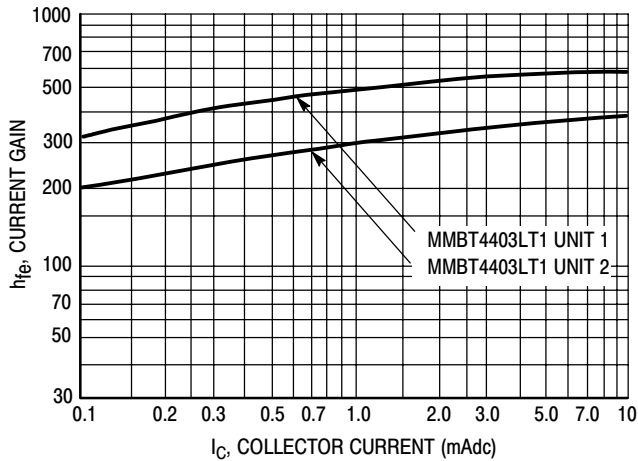


Figure 10. Current Gain

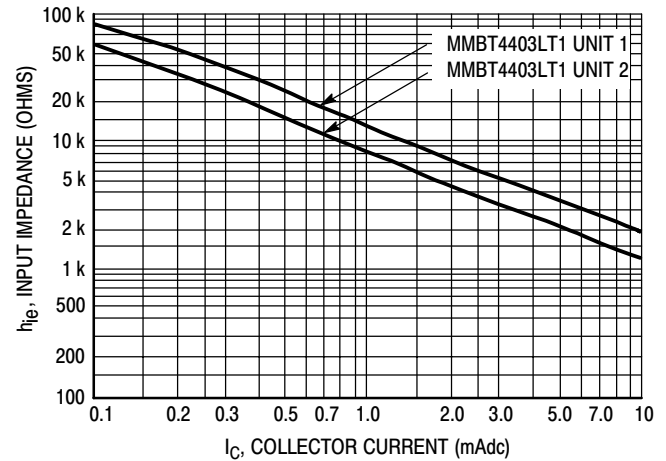


Figure 11. Input Impedance

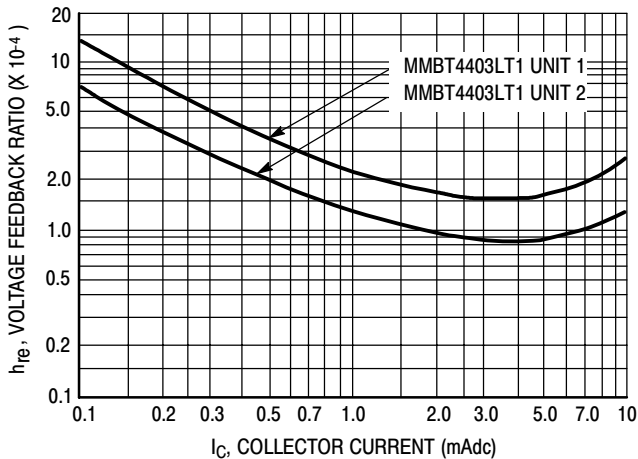


Figure 12. Voltage Feedback Ratio

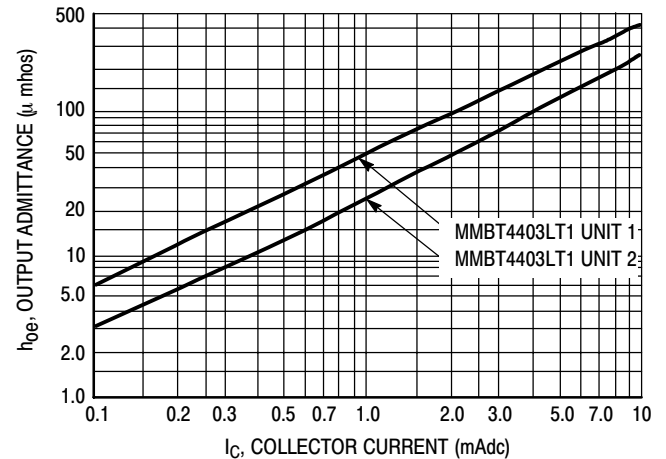


Figure 13. Output Admittance

# MMBT4403LT1

## STATIC CHARACTERISTICS

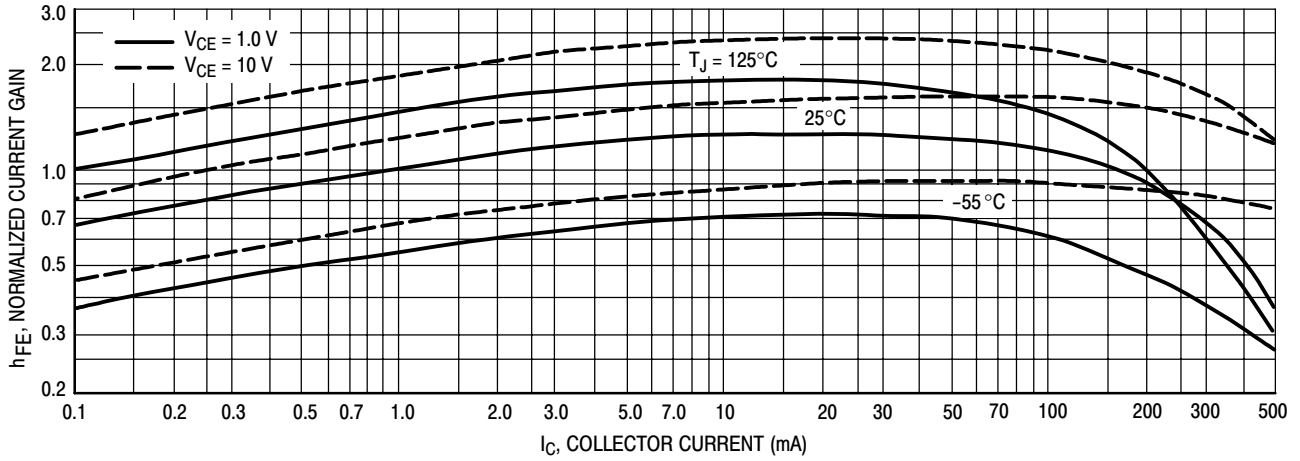


Figure 14. DC Current Gain

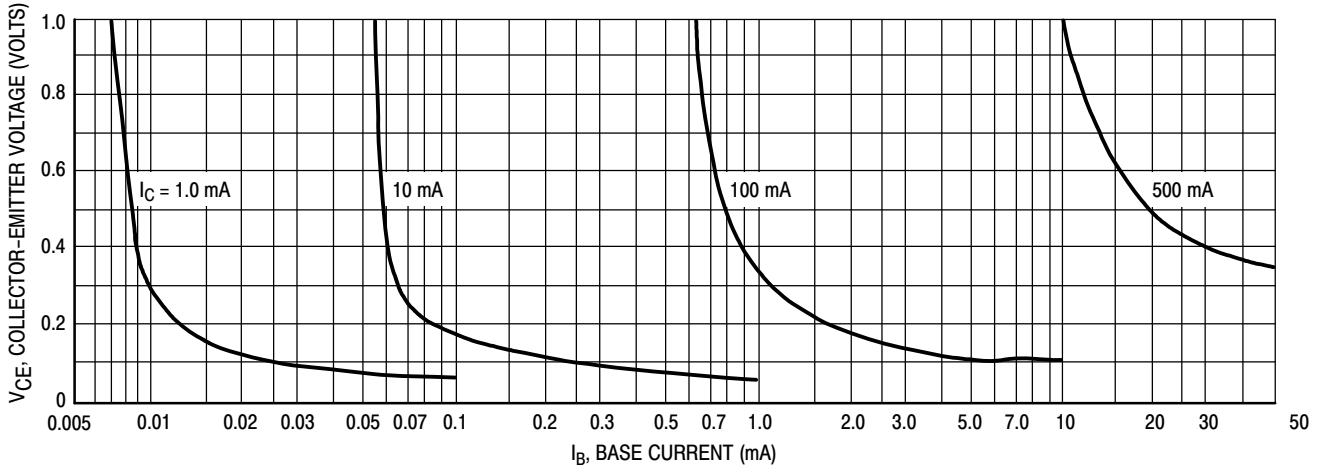


Figure 15. Collector Saturation Region

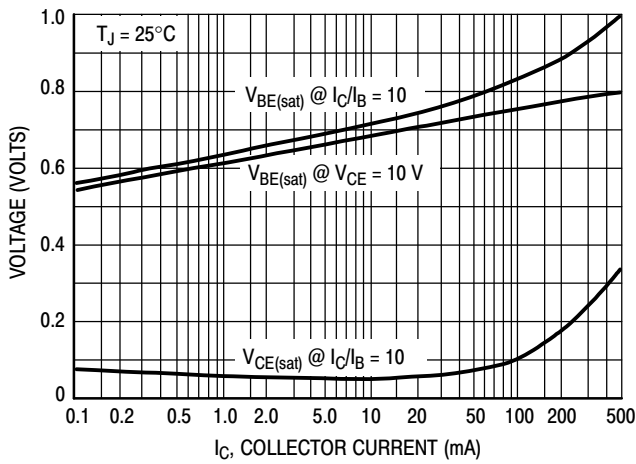


Figure 16. "On" Voltages

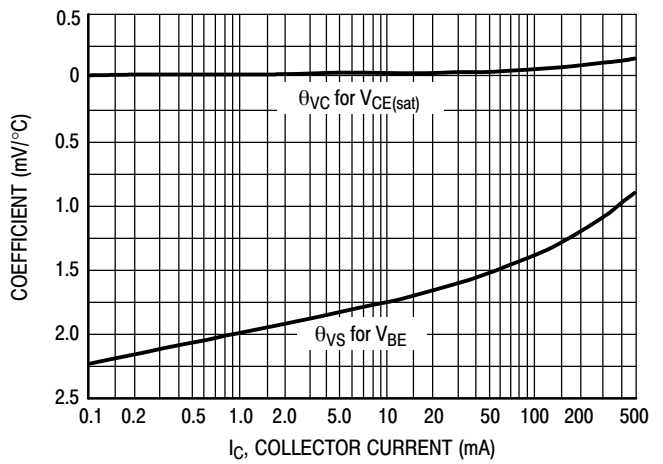
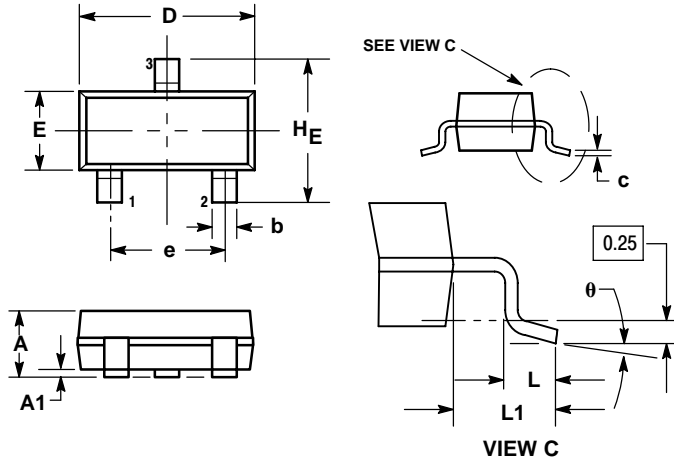


Figure 17. Temperature Coefficients

# MMBT4403LT1

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AN



NOTES:

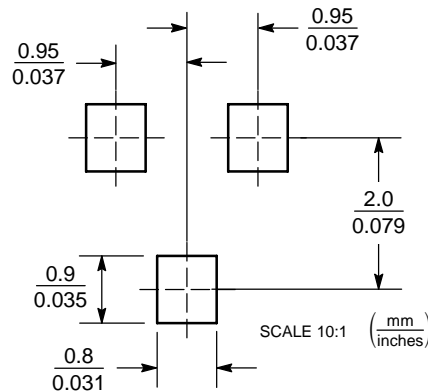
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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